2SB0789, 2SB0789A (2SB789, 2SB789A)

Silicon PNP epitaxial planar type

For low-frequency driver amplification

■ Features

- ullet High collector-emitter voltage (Base open) V_{CEO}
- Large collector power dissipation P_C

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | | |
|-----------------------------|------------------|------------------|------|---|--|
| Collector-base voltage | 2SB0789 | V _{CBO} | -100 | V | |
| (Emitter open) | 2SB0789A | | -120 | | |
| Collector-emitter voltage | 2SB0789 | V _{CEO} | -100 | V | |
| (Base open) | 2SB0789A | | -120 | | |
| Emitter-base voltage (Coll | V_{EBO} | -5 | V | | |
| Collector current | I_{C} | - 0.5 | A | | |
| Peak collector current | I _{CP} | -1 | A | | |
| Collector power dissipation | P _C | 1 | W | | |
| Junction temperature | T _j | 150 | °C | | |
| Storage temperature | T _{stg} | -55 to +150 | °C | | |

Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion.

Unit: mm 4.5±0.1 1.6±0.2 1.5±0.1 1.

Marking Symbol:

- 2SB0789: D
- 2SB0789A

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

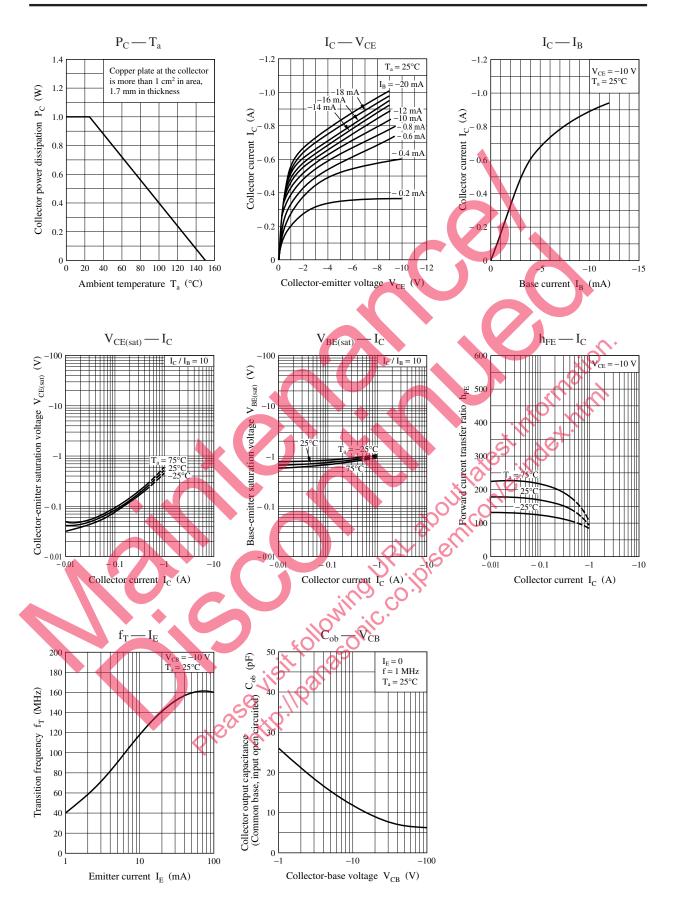
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|--|------|--------|-------|------|
| Collector-emitter voltage 2SB0789 | V _{CEO} | $I_C = -100 \mu A, I_B = 0$ | -100 | | | V |
| (Base open) 2SB0789A | | colle of i | -120 | | | |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_{\rm E} = -10 \text{GA}, I_{\rm C} = 0$ | -5 | | | V |
| Forward current transfer ratio *1 | h _{FE1} *2 | $V_{CE} = 10 \text{ V}, I_{C} = -150 \text{ mA}$ | 90 | | 220 | _ |
| | her2 | $V_{CE} = -5 \text{ V}, I_{C} = -500 \text{ mA}$ | 50 | | | |
| Collector-emitter saturation voltage *1 | V _{CE(sat)} | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$ | | - 0.2 | - 0.6 | V |
| Base-emitter saturation voltage * | V _{BE(sat)} | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$ | | - 0.85 | -1.20 | V |
| Transition frequency | f_T | $V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$ | | 120 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | | 30 | pF |
| (Common base, input open circuited) | | | | | | |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. *1: Pulse measurement
 - *2: Rank classification

| Rank | Q | R |
|------------------|-----------|------------|
| h _{FE1} | 90 to 155 | 130 to 220 |

Note) The part number in the parenthesis shows conventional part number.



2 SJC00056CED

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